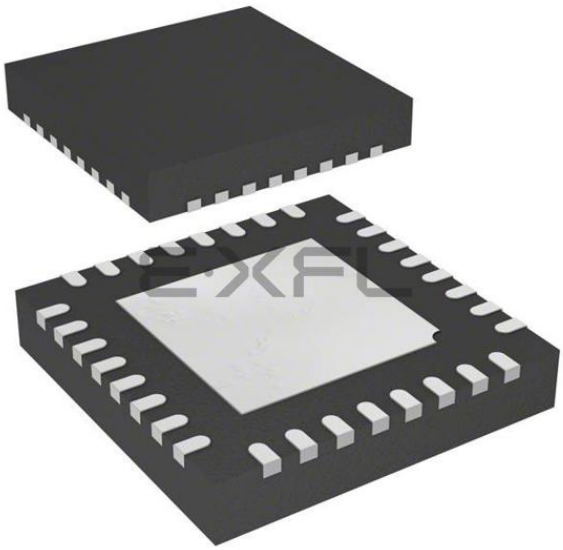

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	24
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 11x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f301k8u7

List of tables

3.4 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.5 Power management

3.5.1 Power supply schemes

- V_{SS}, V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. It is provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supply for ADC, DAC, comparators, operational amplifier, reset blocks, RCs and PLL. The minimum voltage to be applied to V_{DDA} differs from one analog peripheral to another. *Table 3* provides the summary of the V_{DDA} ranges for analog peripherals. The V_{DDA} voltage level must always be greater than or equal to the V_{DD} voltage level and must be provided first.

Table 3. External analog supply values for analog peripherals

Analog peripheral	Minimum V_{DDA} supply	Maximum V_{DDA} supply
ADC/COMP	2.0 V	3.6 V
DAC/OPAMP	2.4 V	3.6 V

- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

3.5.2 Power supply supervisor

The device has an integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 2 V. The device remains in reset mode when the monitored supply voltage is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated Option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.17 Inter-integrated circuit interfaces (I^2C)

The devices feature three I^2C bus interfaces which can operate in multimaster and slave mode. Each I2C interface can support standard (up to 100 kHz), fast (up to 400 kHz) and fast mode + (up to 1 MHz) modes.

All I^2C interfaces support 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask). They also include programmable analog and digital noise filters.

Table 6. Comparison of I2C analog and digital filters

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks
Benefits	Available in Stop mode	1. Extra filtering capability vs. standard requirements. 2. Stable length
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

In addition, it provides hardware support for SMBUS 2.0 and PMBUS 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. It also has a clock domain independent from the CPU clock, allowing the I2Cx (x=1,3) to wake up the MCU from Stop mode on address match.

The I2C interfaces can be served by the DMA controller.

Refer to *Table 7* for the features available in I2C1, I2C2 and I2C3.

Table 7. STM32F301x6/8 I^2C implementation

I2C features(1)	I2C1	I2C2	I2C3
7-bit addressing mode	X	X	X
10-bit addressing mode	X	X	X
Standard mode (up to 100 kbit/s)	X	X	X
Fast mode (up to 400 kbit/s)	X	X	X
Fast Mode Plus with 20mA output drive I/Os (up to 1 Mbit/s)	X	X	X
Independent clock	X	X	X
SMBus	X	X	X
Wakeup from STOP	X	X	X

1. X = supported.

Table 13. STM32F301x6/8 pin definitions (continued)

Pin Number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN32	WLCSP49	LQFP48	LQFP64						
-	-	-	51	PC10	I/O	FT	-	EVENTOUT, SPI3_SCK/I2S3_CK, USART3_TX	-
-	-	-	52	PC11	I/O	FT	-	EVENTOUT, SPI3_MISO/I2S3ext_SD, USART3_RX	-
-	-	-	53	PC12	I/O	FT	-	EVENTOUT, SPI3_MOSI/I2S3_SD, USART3_CK	-
-	-	-	54	PD2	I/O	FT	-	EVENTOUT	-
26	A3	39	55	PB3	I/O	FT	-	JTDO-TRACESWO, TIM2_CH2, TSC_G5_IO1, SPI3_SCK/I2S3_CK, USART2_TX, EVENTOUT	-
27	A4	40	56	PB4	I/O	FT	-	JTRST, TIM16_CH1, TSC_G5_IO2, SPI3_MISO/I2S3ext_SD, USART2_RX, TIM17_BKIN, EVENTOUT	-
28	B4	41	57	PB5	I/O	FT	-	TIM16_BKIN, I2C1_SMBAI, SPI3_MOSI/I2S3_SD, USART2_CK, I2C3_SDA, TIM17_CH1, EVENTOUT	-
29	C4	42	58	PB6	I/O	FTf	-	TIM16_CH1N, TSC_G5_IO3, I2C1_SCL, USART1_TX, EVENTOUT	-
30	D4	43	59	PB7	I/O	FTf	-	TIM17_CH1N, TSC_G5_IO4, I2C1_SDA, USART1_RX, EVENTOUT	-

Table 29. Typical and maximum current consumption from VDD supply at VDD = 3.6V (continued)

Symbol	Parameter	Conditions	f_{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ	Max @ T_A(1)			Typ	Max @ T_A(1)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DD}	Supply current in Run mode, executing from RAM	External clock (HSE bypass)	72 MHz	45.8	49.1(2)	50.1	51.4(2)	25.1	27.3(2)	28.0	28.6(2)	mA
			64 MHz	40.8	43.6	44.9	46.9	22.3	24.1	25.0	25.5	
			48 MHz	30.2	32.9	33.5	34.8	17.0	18.7	19.1	19.6	
			32 MHz	20.5	23.1	24.1	25.4	11.1	12.2	13.2	13.3	
			24 MHz	15.4	17.1	18.3	19.5	8.5	9.7	10.1	10.2	
			8 MHz	5.0	5.9	6.3	6.9	3.1	3.7	4.1	4.7	
			1 MHz	0.8	1.1	1.9	2.6	0.5	0.8	1.2	1.4	
		Internal clock (HSI)	64 MHz	37.3	41.1	41.8	43.3	22.0	23.8	24.4	24.9	
			48 MHz	28.0	31.1	31.6	33.2	16.4	18.0	18.3	18.6	
			32 MHz	18.8	21.3	22.1	23.1	10.9	11.9	12.8	13.1	
			24 MHz	14.2	15.9	16.8	17.9	5.5	6.4	6.7	7.3	
			8 MHz	4.8	5.1	6.0	6.5	2.9	3.5	4.1	4.2	
I_{DD}	Supply current in Sleep mode, executing from Flash or RAM	External clock (HSE bypass)	72 MHz	30.0	32.8(2)	33.1	34.1(2)	5.9	6.8(2)	6.9	7.4(2)	
			64 MHz	26.7	29.2	29.6	30.5	5.3	5.9	6.2	6.7	
			48 MHz	16.7	18.5	19.0	19.7	3.6	4.5	4.5	5.3	
			32 MHz	13.3	14.9	15.3	15.4	2.9	3.7	3.8	4.3	
			24 MHz	10.2	11.4	12.0	12.3	2.2	2.7	2.9	3.2	
			8 MHz	3.6	4.4	4.8	5.3	0.9	1.2	1.5	2.1	
			1 MHz	0.5	0.8	1.1	1.3	0.1	0.4	0.8	0.8	
		Internal clock (HSI)	64 MHz	23.2	25.3	25.6	26.2	5.0	5.7	6.1	6.2	mA
			48 MHz	17.5	19.2	19.4	19.9	3.9	4.7	4.8	5.3	
			32 MHz	11.7	12.9	13.2	13.3	2.6	3.4	3.6	4.2	
			24 MHz	8.9	10.2	10.6	10.8	1.4	2.1	2.4	2.7	
			8 MHz	3.4	4.0	4.6	5.1	0.7	1.1	1.4	1.9	

1. Guaranteed by characterization results.
2. Data based on characterization results and tested in production with code executing from RAM.

Table 32. Typical and maximum V_{DDA} consumption in Stop and Standby modes

Symbol	Parameter	Conditions		Typ @V_{DD} (V_{DD} = V_{DDA})						Max(1)			Unit
				2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DDA}	Supply current in Stop mode	V_{DDA} supervisor ON	Regulator in run/low-power mode, all oscillators OFF	1.70	1.83	1.95	2.08	2.22	2.37	3.40	5.30	5.5	µA
	Supply current in Standby mode		LSI ON and IWDG ON	2.08	2.25	2.41	2.59	2.79	3.01	-	-	-	
			LSI OFF and IWDG OFF	1.59	1.72	1.83	1.96	2.10	2.25	2.80	2.90	3.60	
	Supply current in Stop mode	V_{DDA} supervisor OFF	Regulator in run/low-power mode, all oscillators OFF	0.99	1.01	1.04	1.09	1.14	1.21	-	-	-	
	Supply current in Standby mode		LSI ON and IWDG ON	1.36	1.43	1.50	1.60	1.72	1.85	-	-	-	
			LSI OFF and IWDG OFF	0.87	0.89	0.92	0.97	1.02	1.09	-	-	-	

1. Guaranteed by characterization results.

Table 33. Typical and maximum current consumption from V_{BAT} supply

Symbol	Para meter	Conditions (1)	Typ.@V_{BAT}								Max. @V_{BAT}= 3.6V(2) T_A (°C)			Unit
			1.65V	1.8V	2V	2.4V	2.7V	3V	3.3V	3.6V	25	85	105	
I_{DD_VBAT}	Backup domain supply current	LSE & RTC ON; “Xtal mode” lower driving capability; LSEDRV[1:0] = '00'	0.41	0.43	0.46	0.54	0.59	0.66	0.74	0.82	-	-	-	µA
		LSE & RTC ON; “Xtal mode” higher driving capability; LSEDRV[1:0] = '11'	0.65	0.68	0.73	0.80	0.87	0.95	1.03	1.14	-	-	-	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a CL of 6 pF for typical values.
2. Guaranteed by characterization results.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 54: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 37: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

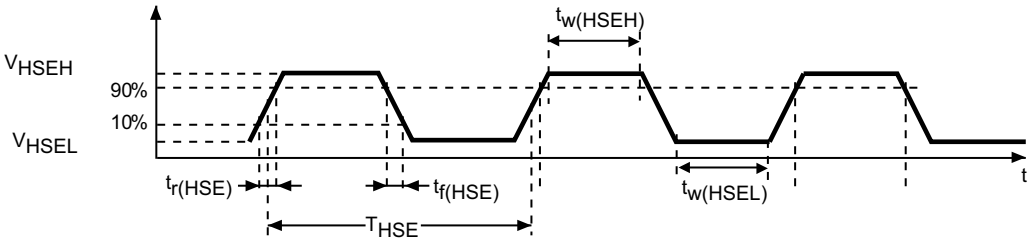
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 14*.

Table 40. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency(1)	-	1	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time(1)		15	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	20	

1. Guaranteed by design.

Figure 14. High-speed external clock source AC timing diagram



6.3.8 Internal clock source characteristics

The parameters given in *Table 44* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 23*.

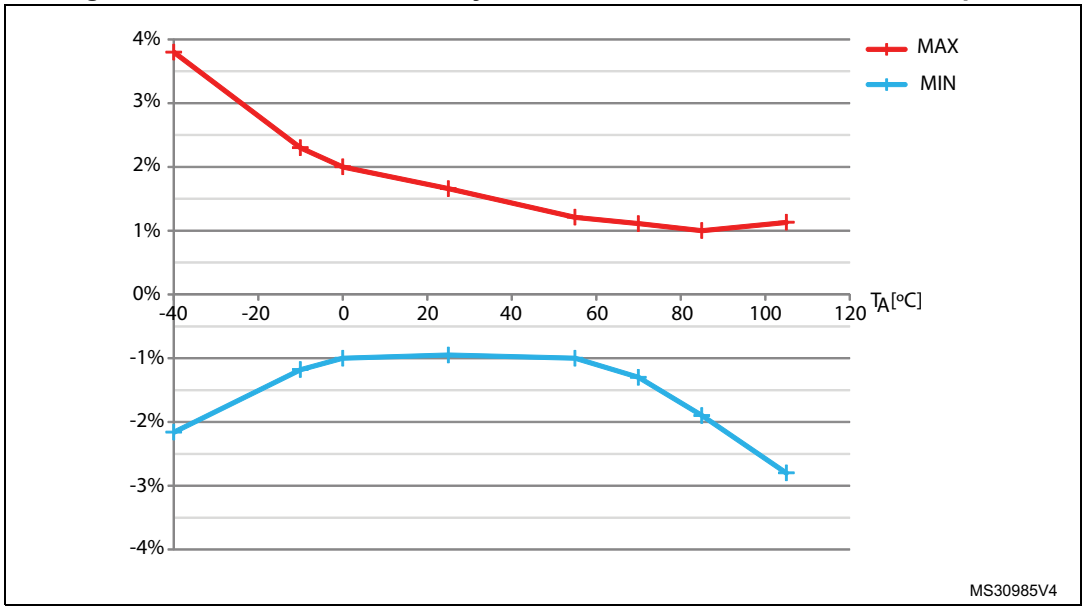
High-speed internal (HSI) RC oscillator

Table 44. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	8	-	MHz
TRIM	HSI user trimming step	-	-	-	1(2)	%
$DuCy_{(HSI)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI}	Accuracy of the HSI oscillator	T_A = -40 to 105°C	-2.8(3)	-	3.8(3)	%
		T_A = -10 to 85°C	-1.9(3)	-	2.3(3)	
		T_A = 0 to 85°C	-1.9(3)	-	2(3)	
		T_A = 0 to 70°C	-1.3(3)	-	2(3)	
		T_A = 0 to 55°C	-1(3)	-	2(3)	
		T_A = 25°C(4)	-1	-	1	
$t_{su(HSI)}$	HSI oscillator startup time	-	1(2)	-	2(2)	µs
$I_{DDA(HSI)}$	HSI oscillator power consumption	-	-	80	100(2)	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design.
3. Guaranteed by characterization results.
4. Factory calibrated, parts not soldered.

Figure 18. HSI oscillator accuracy characterization results for soldered parts



6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 49*. They are based on the EMS levels and classes defined in application note AN1709.

Table 49. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_A = +25°C, f_{HCLK} = 72 MHz conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_A = +25°C, f_{HCLK} = 72 MHz conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 50. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/72 MHz	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP64 package compliant with IEC 61967-2	0.1 to 30 MHz	5	dBµV
			30 to 130 MHz	6	
			130 MHz to 1GHz	28	
			SAE EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 51. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Packages	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	All	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	LQFP64, WLCSP49	C3	250	V
			All other	C4	500	

1. Guaranteed by characterization results.

Figure 30 illustrates the ADC current consumption as per the clock frequency in single-ended and differential modes.

Figure 30. ADC typical current consumption in single-ended and differential modes

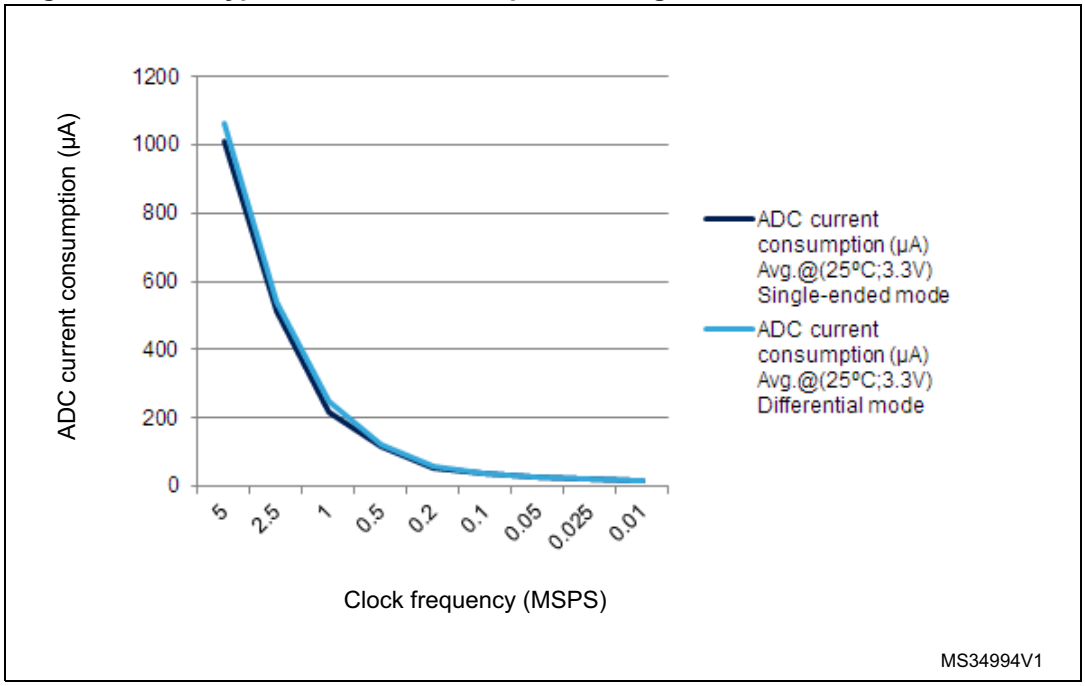


Table 65. Maximum ADC R_{AIN} (1)

Resolution	Sampling cycle @ 72 MHz	Sampling time [ns] @ 72 MHz	R_{AIN} max (kΩ)		
			Fast channels(2)	Slow channels	Other channels(3)
12 bits	1.5	20.83	0.018	NA	NA
	2.5	34.72	0.150	NA	0.022
	4.5	62.50	0.470	0.220	0.180
	7.5	104.17	0.820	0.560	0.470
	19.5	270.83	2.70	1.80	1.50
	61.5	854.17	8.20	6.80	4.70
	181.5	2520.83	22.0	18.0	15.0
	601.5	8354.17	82.0	68.0	47.0

Table 66. ADC accuracy - limited test conditions(1)(2) (continued)

Symbol	Parameter	Conditions			Min (3)	Typ	Max (3)	Unit
SNR(4)	Signal-to-noise ratio	ADC clock freq. ≤ 72 MHz Sampling freq ≤ 5 Msps V_{DDA} = 3.3 V 25°C	Single ended	Fast channel 5.1 Ms	66	67	-	dB
				Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	
THD(4)	Total harmonic distortion		Single ended	Fast channel 5.1 Ms	-	-80	-80	
				Slow channel 4.8 Ms	-	-78	-77	
			Differential	Fast channel 5.1 Ms	-	-83	-82	
				Slow channel 4.8 Ms	-	-81	-80	

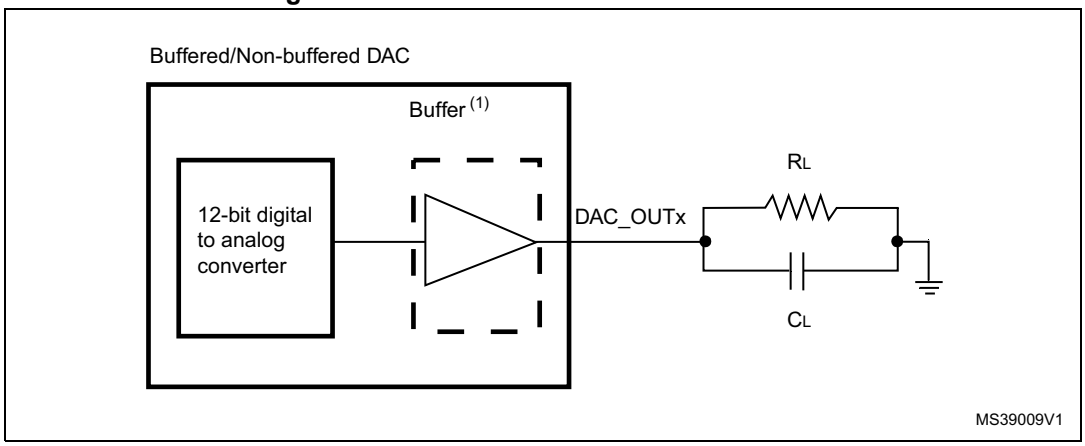
1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.14* does not affect the ADC accuracy.
3. Guaranteed by characterization results.
4. Value measured with a –0.5dB Full Scale 50kHz sine wave input signal.

Table 69. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Update rate(3)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ	-	-	1	MS/s
t_{WAKEUP}(3)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ	-	6.5	10	µs
PSRR+ (1)	Power supply rejection ratio (to V_{DDA}) (static DC measurement	$C_{LOAD} = 50$ pF, No $R_{LOAD} \geq 5$ kΩ,	-	–67	–40	dB

1. Guaranteed by design.
2. Quiescent mode refers to the state of the DAC a keeping steady value on the output, so no dynamic consumption is involved.
3. Guaranteed by characterization results.

Figure 33. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.20 Comparator characteristics

Table 70. Comparator characteristics(1)(2)

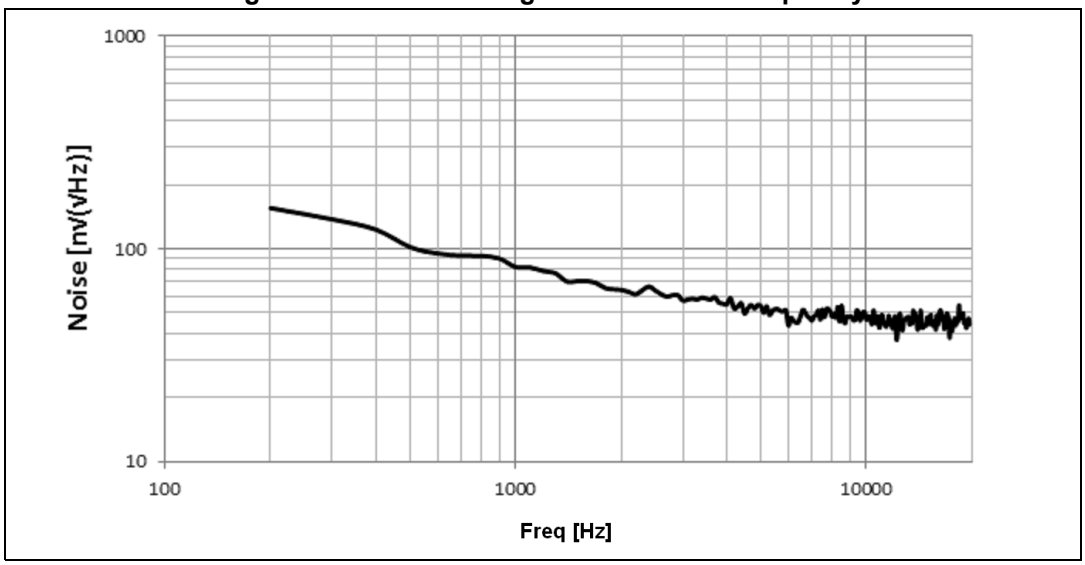
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{DDA}	Analog supply voltage	-	2	-	3.6	V
V_{IN}	Comparator input voltage range	-	0	-	V_{DDA}	V
V_{BG}	Scaler input voltage	-	-	$V_{REFINIT}$	-	
V_{SC}	Scaler offset voltage	-	-	±5	±10	mV

6.3.21 Operational amplifier characteristics

Table 71. Operational amplifier characteristics(1)

Symbol	Parameter		Condition	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage		-	2.4	-	3.6	V
CMIR	Common mode input range		-	0	-	V_{DDA}	V
VI_{OFFSET}	Input offset voltage	Maximum calibration range	25°C, No Load on output.	-	-	4	mV
			All voltage/Temp.	-	-	6	
		After offset calibration	25°C, No Load on output.	-	-	1.6	
			All voltage/Temp.	-	-	3	
ΔVI_{OFFSET}	Input offset voltage drift		-	-	5	-	µV/°C
I_{LOAD}	Drive current		-	-	-	500	µA
IDDOPAMP	Consumption		No load, quiescent mode	-	690	1450	µA
CMRR	Common mode rejection ratio		-	-	90	-	dB
PSRR	Power supply rejection ratio		DC	73	117	-	dB
GBW	Bandwidth		-	-	8.2	-	MHz
SR	Slew rate		-	-	4.7	-	V/µs
R_{LOAD}	Resistive load		-	4	-	-	kΩ
C_{LOAD}	Capacitive load		-	-	-	50	pF
VOH_{SAT}	High saturation voltage(2)		R_{load} = min, Input at V_{DDA}.	V_{DDA}-100	-	-	mV
			R_{load} = 20K, Input at V_{DDA}.	V_{DDA}-20	-	-	
VOL_{SAT}	Low saturation voltage(2)		Rload = min, input at 0V	-	-	100	
			Rload = 20K, input at 0V.	-	-	20	
φm	Phase margin		-	-	62	-	°
$t_{OFFTRIM}$	Offset trim time: during calibration, minimum time needed between two steps to have 1 mV accuracy		-	-	-	2	ms
t_{WAKEUP}	Wake up time from OFF state.		C_{LOAD} ≤50 pf, R_{LOAD} ≥ 4 kΩ, Follower configuration	-	2.8	5	µs
$t_{S\_OPAM\_VOUT}$	ADC sampling time when reading the OPAMP output			400	-	-	ns

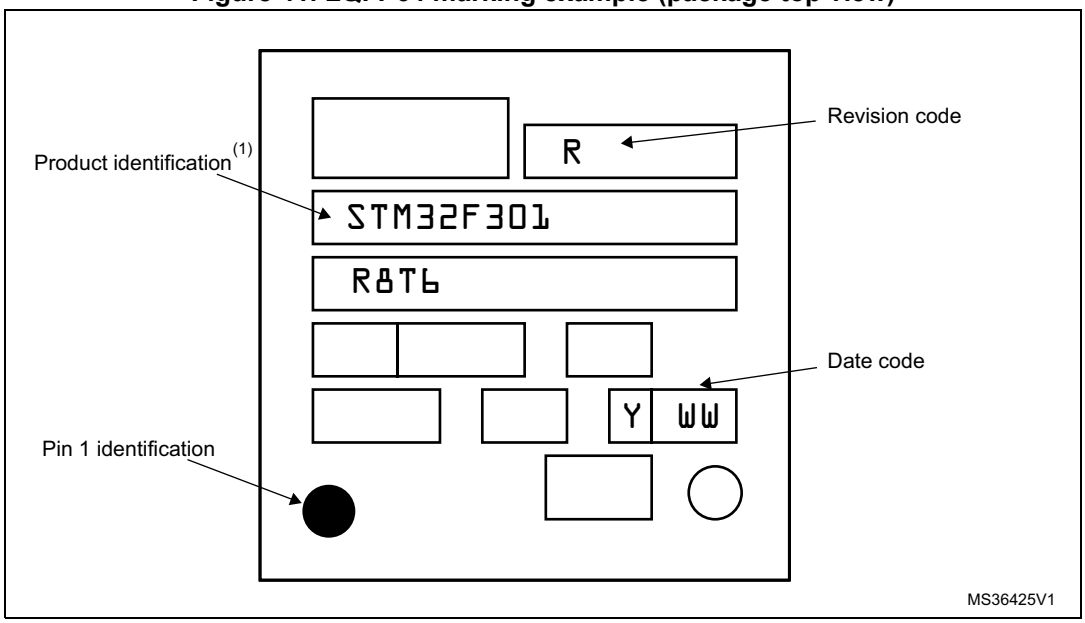
Figure 35. OPAMP Voltage Noise versus Frequency



Device marking

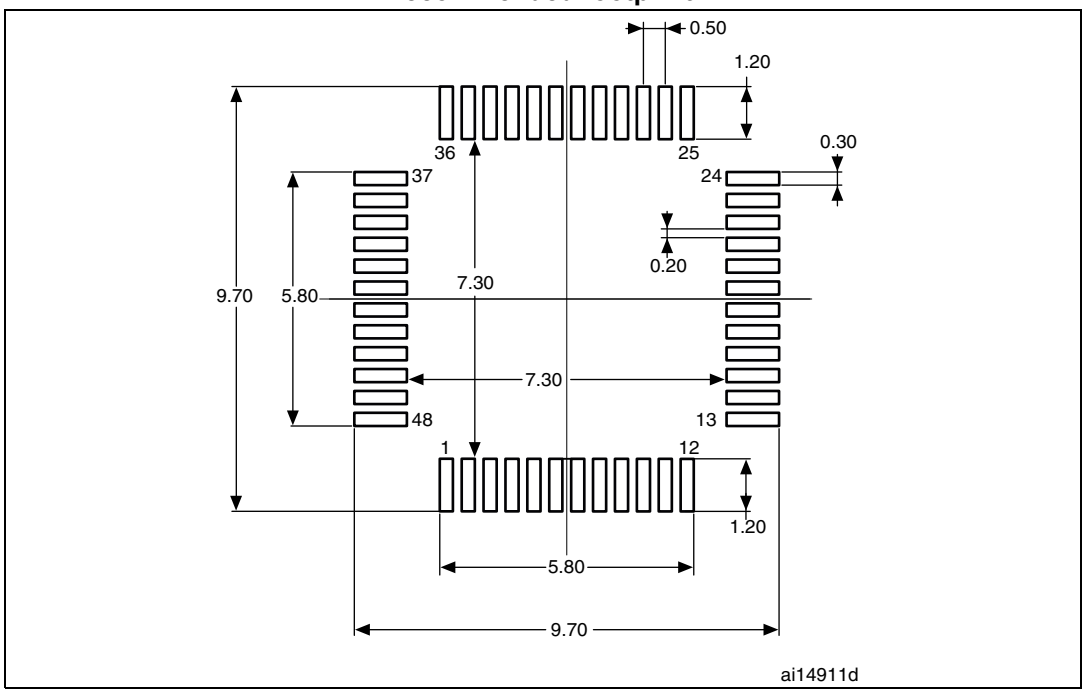
The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 41. LQFP64 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

7.5 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 23: General operating conditions*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 80. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP64 - 10 × 10 mm / 0.5 mm pitch	45	°C/W
	Thermal resistance junction-ambient LQFP48 - 7 × 7 mm	55	
	Thermal resistance junction-ambient WCSP49 - 3.4 x 3.4 mm	49	
	Thermal resistance junction-ambient UFQFN32 - 5 x 5 mm	37	

7.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org